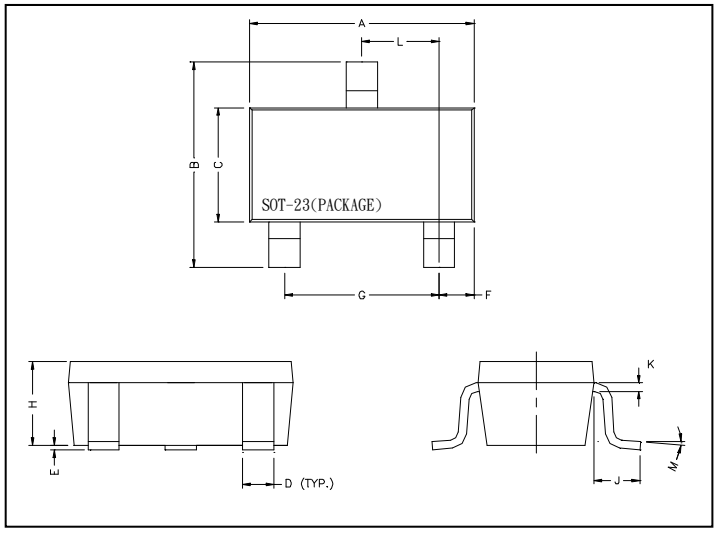
G491SD

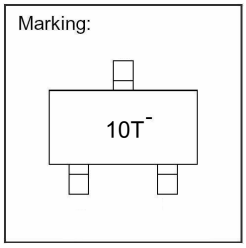
SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 25V, CURRENT 1A

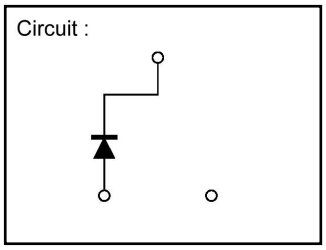
Description

The G491SD is low power rectification for switching power supply.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90 REF.	
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

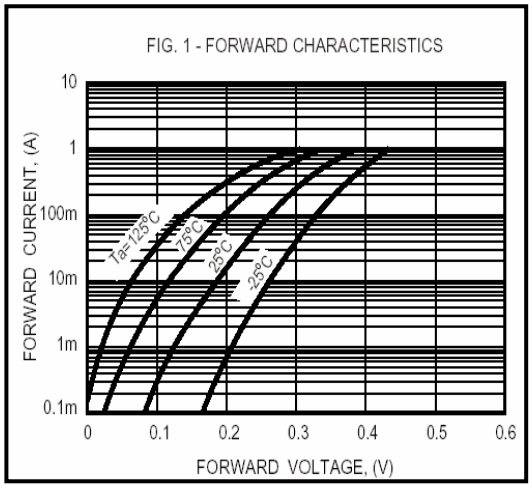
Absolute Maximum Ratings at Ta = 25℃

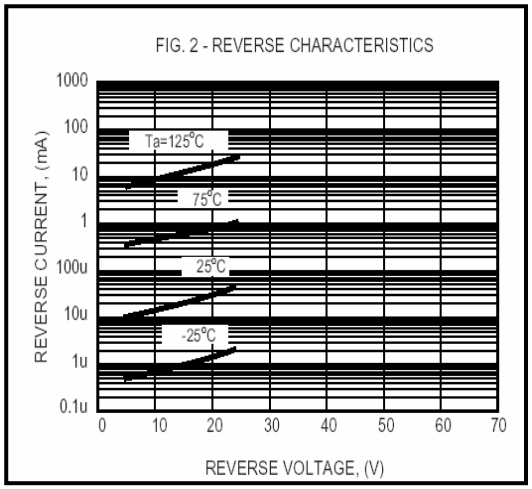
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	℃
Storage Temperature	Tstg	-40 ~ +125	℃
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	25	V
Maximum RMS Voltage	V_{RMS}	18	V
Maximum DC Blocking Voltage	V_{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I_{FSM}	3	A
Typical Junction Capacitance between Terminal	C_J	30	pF
Maximum Average Forward Rectified Current	Io	1.0	A
Total Power Dissipation	PD	225	mW

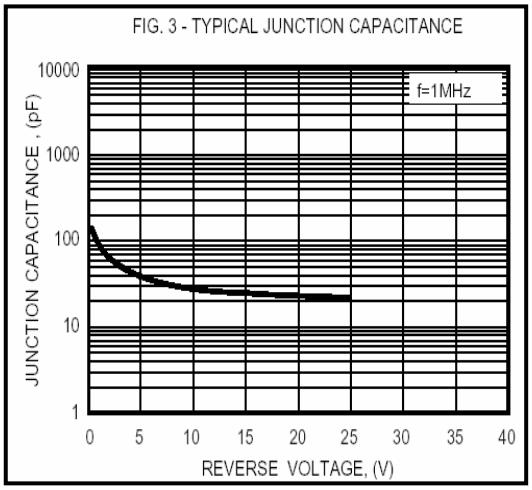
Characteristics at Ta = 25℃

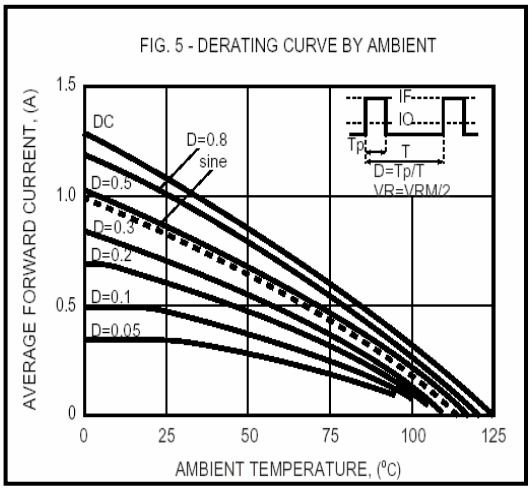
Characteristics	Symbol	Min.	Max.	Unit	Test Condition
Reverse breakdown voltage	V(BR)R	25	-	V	IR = 100uA
Maximum Instantaneous Forward Voltage	V_F	-	0.45	V	IF = 1A
Maximum Average Reverse Current	IR	-	200	uA	VR = 20V

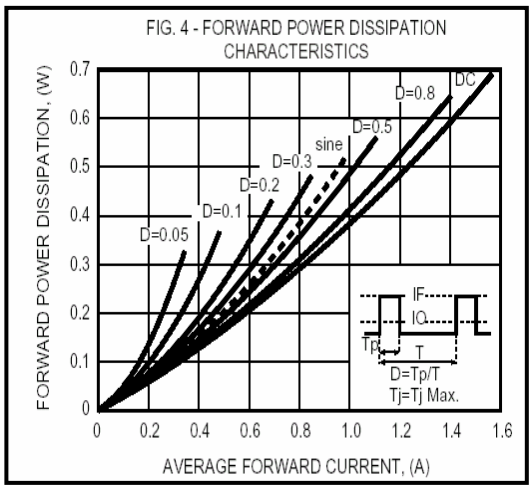
Characteristics Curve











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